

Si Substrate

Thickness : 3.5 μ m

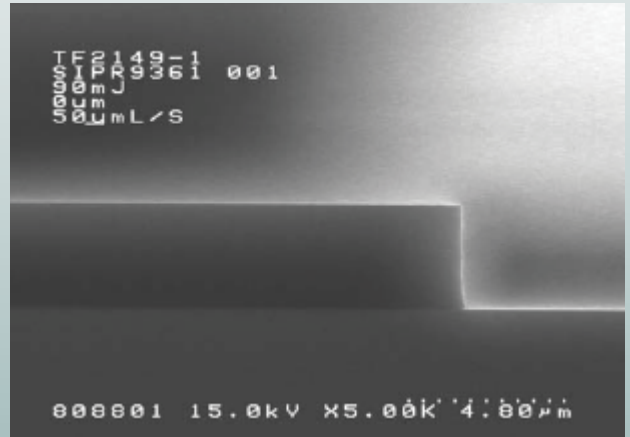
Exposure : NIKON NSR1755i7A (Na=0.50, σ =0.60) ;90mJ

PEB : None

Prebake : 100°C x 120 sec

Dev :50sec x 2 puddles (SSFD-238)

50 μ m L/S



Post Bake : 180°C/2 Hrs

